AN INSULATED GATE FIELD EFFECT TRANSISTOR

ABSTRACT

An FET isolated on either side by a trench (120). The FET has a dielectric layer in the isolating trench along at least one side. The dielectric layer which may be an ONO layer (128) has an oxidation catalyst diffused into it. The oxidation catalyst may be potassium. Gate oxide along the side (142) of the FET in close proximity to the ONO layer (128) is thicker than gate oxide between both sides.

Fig. 2F